Xiaoyan Wu

List of Publications by Year in descending order

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#	Article	IF	CITATIONS
1	Amorphous monodispersed hard carbon micro-spherules derived from biomass as a high performance negative electrode material for sodium-ion batteries. Journal of Materials Chemistry A, 2015, 3, 71-77.	10.3	432
2	Unraveling the storage mechanism in organic carbonyl electrodes for sodium-ion batteries. Science Advances, 2015, 1, e1500330.	10.3	170
3	A spray drying approach for the synthesis of a Na ₂ C ₆ H ₂ O ₄ /CNT nanocomposite anode for sodium-ion batteries. Journal of Materials Chemistry A, 2015, 3, 13193-13197.	10.3	75
4	1.142 μm GaAsBi/GaAs Quantum Well Lasers Grown by Molecular Beam Epitaxy. ACS Photonics, 2017, 4, 1322-1326.	6.6	37
5	Vibrational properties of epitaxial Bi4Te3 films as studied by Raman spectroscopy. AIP Advances, 2015, 5,	1.3	20
6	Negative thermal quenching of below-bandgap photoluminescence in InPBi. Applied Physics Letters, 2017, 110, .	3.3	19
7	Raman spectroscopy of epitaxial topological insulator Bi2Te3 thin films on GaN substrates. Modern Physics Letters B, 2015, 29, 1550075.	1.9	18
8	Growth and material properties of InPBi thin films using gas source molecular beam epitaxy. Journal of Alloys and Compounds, 2016, 656, 777-783.	5.5	17
9	Effect of thermal annealing on structural properties of GeSn thin films grown by molecular beam epitaxy. AIP Advances, 2017, 7, .	1.3	17
10	Scalable non-invasive imaging through dynamic scattering media at low photon flux. Optics and Lasers in Engineering, 2021, 144, 106641.	3.8	12
11	Optical properties and band bending of InGaAs/GaAsBi/InGaAs type-II quantum well grown by gas source molecular beam epitaxy. Journal of Applied Physics, 2016, 120, 105702.	2.5	10
12	Anomalous photoluminescence in InP1â^'xBix. Scientific Reports, 2016, 6, 27867.	3.3	10
13	Growth of semiconductor alloy InGaPBi on InP by molecular beam epitaxy. Semiconductor Science and Technology, 2015, 30, 094006.	2.0	8
14	Investigation to the deep center related properties of low temperature grown InPBi with Hall and photoluminescence. AIP Advances, 2015, 5, 127104.	1.3	5
15	Electrically injected GaAsBi/GaAs single quantum well laser diodes. AIP Advances, 2017, 7, 115006.	1.3	5
16	Regulating the Single-Mode Lasing Intensity of Semiconductor Lasers Without Wavelength Shift. IEEE Photonics Journal, 2020, 12, 1-9.	2.0	1
17	Photon limited imaging through disordered media: information extraction by exploiting the photon's quantum nature via deep learning. Applied Physics B: Lasers and Optics, 2022, 128, 1.	2.2	1